Abstracts

Phase Distortion Mechanism of a GaAs FET Power Amplifier for Digital Cellular Application

H. Ikeda, T. Ishizaki, Y. Yoshikawa, T. Uwano and K. Kanazawa. "Phase Distortion Mechanism of a GaAs FET Power Amplifier for Digital Cellular Application." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 541-544.

A conventional class AB amplifier with high efficiency has had phase distortion which is not suitable for pi/4-shift QPSK signal. A simple FET model including four non-linear elements is presented to explain the distortion mechanism. By using those parameters, a class AB amplifier with low phase variation of less than 2 degrees is designed.

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